

IN THE CLAIMS:

1. (Original) A semiconductor light emitting device comprising:
 - a substrate;
 - a semiconductor multilayer structure formed on a first main surface of the substrate, the semiconductor multilayer structure including a light emitting layer;
 - a first electrode and a second electrode formed on the semiconductor multilayer structure, power being supplied to the semiconductor multilayer structure through the first electrode and the second electrode so as to cause the light emitting layer to emit light;
 - a phosphor film covering at least a main surface of the semiconductor multilayer structure which faces away from the first main surface of the substrate;
 - a first terminal and a second terminal formed on a second main surface of the substrate;
 - a first conductive member electrically connecting the first electrode to the first terminal; and
 - a second conductive member electrically connecting the second electrode to the second terminal.
2. (Original) The semiconductor light emitting device of Claim 1, wherein
 - at least part of each of the first conductive member and the second conductive member is a plated-through hole provided in the substrate.
3. (Original) The semiconductor light emitting device of Claim 2, wherein
 - the semiconductor multilayer structure is divided into a plurality of portions by a division groove that is deep enough to reach the substrate, and

each of the plurality of portions is constituted as an independent light emitting element.

4. (Original) The semiconductor light emitting device of Claim 3, wherein the light emitting element has a diode structure, and includes an anode electrode and a cathode electrode,

a plurality of light emitting elements are connected in series in such a manner that a cathode electrode of a light emitting element is connected to an anode electrode of a different light emitting element using a wire formed by a thin metal film, and

an anode electrode of a light emitting element at a higher potential end of an array of the plurality of light emitting elements is constituted as the first electrode, and a cathode electrode of a light emitting element at a lower potential end of the array is constituted as the second electrode.

5. (Original) The semiconductor light emitting device of Claim 1, wherein at least part of each of the first conductive member and the second conductive member is a conductive film formed on a side surface of the substrate.

6. (Original) The semiconductor light emitting device of Claim 5, wherein the semiconductor multilayer structure is divided into a plurality of portions by a division groove that is deep enough to reach the substrate, and each of the plurality of portions is constituted as an independent light emitting element.

7. (Original) The semiconductor light emitting device of Claim 6, wherein
the light emitting element has a diode structure, and includes an anode electrode
and a cathode electrode,
a plurality of light emitting elements are connected in series in such a manner that
a cathode electrode of a light emitting element is connected to an anode electrode of a different
light emitting element using a wire formed by a thin metal film, and
an anode electrode of a light emitting element at a higher potential end of
an array of the plurality of light emitting elements is constituted as the first electrode, and a
cathode electrode of a light emitting element at a lower potential end of the array is constituted
as the second electrode.

8. (Currently Amended) A lighting module comprising:
a mounting substrate; and
a semiconductor light emitting device defined in ~~one of Claims 1 to 5~~ Claim 1,
wherein
the semiconductor light emitting device is mounted on the mounting substrate in
such a manner that a first terminal and a second terminal are faced to the mounting substrate.

9. (Original) The lighting module of Claim 8 further comprising:
a reflective mirror surrounding a semiconductor multilayer structure of the
semiconductor light emitting device so as to reflect light emitted from a side surface of the
semiconductor multilayer structure in a direction substantially perpendicular to a first main
surface of a substrate.

10. (Original) The lighting module of Claim 9, wherein
the mounting substrate has a depression which increases in diameter from a
bottom to an open end,
the reflective mirror is a reflective film provided on a wall of the depression, and
the semiconductor light emitting device is mounted on the bottom of the
depression.
11. (Original) A lighting apparatus including a lighting module defined in Claim 8 as
a light source.
12. (Currently Amended) A display element including a semiconductor light emitting
device defined in ~~one of Claims 1 to 5~~ Claim 1 as a light source.
13. (Original) A manufacturing method for a semiconductor light emitting device,
comprising steps of:
forming a semiconductor multilayer structure including a light emitting layer on
one of main surfaces of a substrate;
dividing the semiconductor multilayer structure into a plurality of portions each of
which corresponds to the semiconductor light emitting device;
forming a phosphor film on and around each of the plurality of portions of the
semiconductor multilayer structure; and
dividing the substrate for each of the plurality of portions.